Phase transitions and ferroelectricity in very thin films: single- versus multidomain state

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We discuss ferroelectric phase transitions into single- and multidomain states in very thin films using continuous theory. It is shown that in nearly cubic ferroelectrics the domain state may survive down to atomic film thicknesses, unlike the single domain state, which is almost always unstable or metastable. This conclusion is valid almost irrespective of the nature of electrodes (metallic or semiconducting) and whether or not the screening carriers may be present in the ferroelectric itself.

With a thrust towards developing nanoelectronics components, like ferroelectric (FE) memories [1] the question of phase transformation and the very existence of ferroelectricity (problem of "critical thickness", first raised decades ago [2–5]) becomes ever more important. It is a focus of experimental and theoretical research, see e.g. [6,7]. Here we will present the thermodynamic results for phase behavior of ferroelectric thin films with various electrodes and consider both homogeneous and inhomogeneous states of the film as a function of temperature and thickness. Many of prior works have given some results almost exclusively for homogeneous (monodomain) ferroelectric film states [2–5,8] with estimates for a "critical thickness" ranging from 1 m [2] to a few nm [8]. We shall call critical the thickness where either homogeneous or inhomogeneous spontaneous polarization becomes unfavorable. Obviously, it is non-universal, and depends on many details like the ferroelectric material, lattice mismatch, type of electrodes, etc. For instance, we show below that the homogeneous state studied in Ref. [7] may exist only when very special conditions are met, in most real situations the FE films are likely metastable or even unstable with regards to breaking into domains. Importantly, ferroelectric domains in nearly unstrained cubic FE films may exist down to practically one unit cell.

Consider a slab of uniaxial ferroelectric occupying the region $-l/2 < z < l/2$ between two metallic (or degenerate semiconductor) electrodes. The polar axis is perpendicular to the film plane (parallel to the z axis), and the bias voltage is set as $(+)U/2$ at the right (left) electrode: The electric field would penetrate into electrode over very short Thomas-Fermi screening length [9], and this screening layer manifest itself as some additional "interface capacitance" [10]. To characterize the screening, we introduce the band bending potential as $' = \quad U/2$. Since the screening is assumed to be very efficient, the potential drop in the electrode is small compared to the Fermi energy , $j_1 j = \quad 1$; and the Poisson equation linearizes to $'' = \quad ^2$; where $= \sqrt{6\,nq^2/\varepsilon_s}$ is the inverse screening length, $^{-1} = 0.5 \quad 0.7$ A in metals [9], comparable to the atomic distance d_{at}; n the net carrier density, ε_s the dielectric constant, q the elementary charge. According to this equation, the band bending is antisymmetric, $'(-z) = \quad '(z)$; $' = \quad _1 e^{-(z-l/2)}$ at $z > l/2$, with

$$_1 = (2\,P\,l + U/2)/(1 + \varepsilon_s\,l/2): \qquad (1)$$

This is the local electrodynamic boundary condition. In fact, the surface has properties different from the bulk and generally produces an effective "field" w coupled to the normal component of polarization, as was pointed out recently [11]. This, in principle, requires to add to (1) the additional boundary conditions for polarization [12,13,10,11]. The solution (1) applies when $j_{q\ 1}j \quad$; that translates for metal, where $l \quad l = d_{at} \quad 1$; into $4\ qjPj = \quad 4\ qjPj\varepsilon_{at} \quad$; which is always satisfied. The condition would be violated in moderately/lightly doped semiconductors.

The equation of state of a ferroelectric

$$AP + BP^3 = E; \qquad (2)$$

where the homogeneous field in the monodomain ferroelectric would be $E = (\varepsilon_s U \quad 8\,P)/(\varepsilon_s\,l + 2)$; $A = (T \quad T_c)/T_0$, T_c is the critical temperature, T_0 the characteristic temperature, $T_0 \quad T_{at}$ in displacive ferroelectrics, where $T_{at} \quad 10^4 \quad 10^5$K is the characteristic "atomic" temperature. The field $E = E_0 + E_d$; where $E_0 = U/l$ is the external and

$$E_d = \quad P\,L_0/l \qquad (3)$$

is the depolarizing field, $L_0 = 8\,\varepsilon_s$ the characteristic length scale in electrodes, and we have used the fact that in a metal the screening length is small, $l \quad 1$: The homogeneous ferroelectric state in short-circuited electrodes, $U = 0$; requires an intersection of the $P(E)$ curves given by Eqs. (2) and (3) at $P \neq 0$ (Fig. 1). This necessary, but not sufficient, condition is realized at

$$A < A_h \quad L_0/l; \qquad (4)$$

illustrated in Fig. 1a, where curves 1–3 are plotted for $T_1 > T_2 > T_3$: The nontrivial solutions exist only for

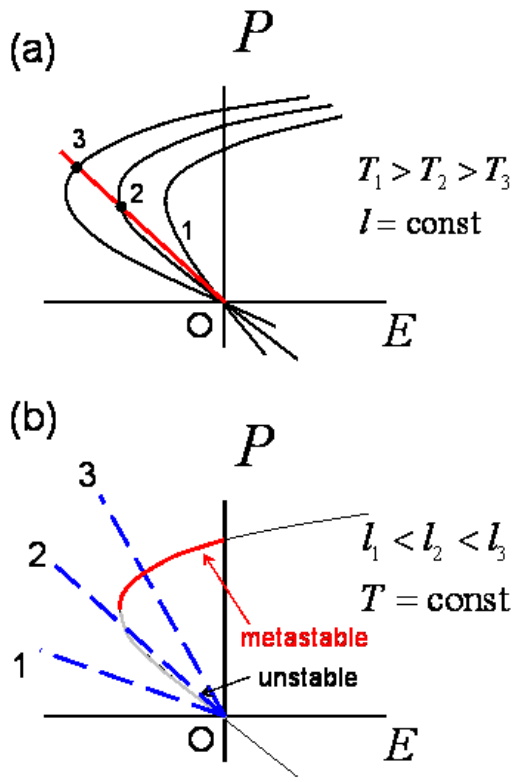

FIG. 1. Solutions of the equation of state for FE film (2) with the depletion field E_d (3): (a) at constant thickness of the film and decreasing temperature; (b) at constant temperature T and varying thickness l. Nontrivial solutions, when they exist, are either unstable (2) or metastable (3) with respect to domains.

$T_{2,3}$. If these solutions were stable with respect to formation of inhomogeneous states, the corresponding critical temperature would be suppressed by $T_c - T_0 L_0/l \sim T_0 d_{at}/\xi_s l$, compared to the bulk T_c [4,10]. Hence, the homogeneous ferroelectricity would become impossible in films with a thickness below

$$l_{hc} \sim \xi_s |A|_{max} = L_0 T_0/T_c; \qquad (5)$$

where $|A|_{max} = T_c/T_0$. In displacive systems $|A|_{max} \sim 10^{-2} - 10^{-3}$, so for $\xi_s \sim 1 - 10$ and $d_{at} \sim 1$ we find $l_{hc} \sim 10^2 - 10^3\, d_{at} \sim 50 - 500$Å. One should bear in mind that the ferroelectricity was observed in thinner films [6] but it was not possible to check if the film was mono- or polydomain, the latter being much more likely scenario. Obviously, when the external field is larger than the depolarizing field (3), $E_0 > E_d$, the film will be in monodomain state. This indicates the boundary between poly- and monodomain states and correctly describes the tilt of the hysteresis loops with decreasing film thickness observed in Ref. [6].

The necessity to study the sufficient conditions is suggested by Fig. 1, since the homogeneous ferroelectric solution belongs in the regions which correspond to either unstable or metastable states in the bulk samples. The problem of stability loss with respect to small fluctuations is a nontrivial yet tractable (linear) problem [14,15]. The check on metastability requires the calculation of free energies, which are much more difficult to find, so only limiting cases will be discussed below. The question of stability with respect to small fluctuations splits into two parts: stability with respect to (i) homogeneous and (ii) inhomogeneous fluctuations. Any solution of Eqs. (2) and (3) is stable with regards to homogeneous fluctuations. One can prove this by solving a relaxation dynamics for polarization constructed by generalizing the equation of state (2):

$$\frac{\partial P}{\partial t} = -\tilde{A}P - BP^3; \qquad (6)$$

where the relaxation parameter $\gamma > 0$. Linearizing this equation about the point $P = P_0$, where

$$P_0 = \sqrt{-\tilde{A}/B}; \quad \tilde{A} = A + L_0/l; \qquad (7)$$

one obtains for homogeneous fluctuations $\delta P = P - P_0$

$$\frac{\partial\, \delta P}{\partial t} = -\tilde{A} + 3BP_0^2 \quad \delta P; \qquad (8)$$

so that the perturbation does indeed decay with time as $\delta P \propto e^{-\gamma t}$ with the decrement $\gamma = 2\tilde{A} < 0$.

Now let us discuss stability with respect to inhomogeneous fluctuations of polarization. The present situation with the field penetrating into electrode over the Thomas-Fermi length is analogous to a ferroelectric film separated from the electrodes by nonferroelectric "dead" layers [16,17,14] that promote breaking the film into domains. To obtain the conditions for domain instability in the present case, one looks for a nontrivial solution of the equation of state with the gradient term included [15]

$$AP + BP^3 - gr_\perp^2 P = E; \qquad (9)$$

where $r_\perp^2 = \partial_x^2 + \partial_y^2$ is "in-plane" Laplacian, together with Maxwell equations. The solution is sought in a form of a "polarization wave" $P = P_0 + \delta P_k(z)e^{ikx}$; $\Phi = \Phi_k(z)e^{ikx}$, where $\delta P_k(z)$ is the small perturbation over the homogeneous polarization P_0 [14;15]. In the case of metallic screening we obtain the following condition for an existence of the nontrivial solution with certain k:

$$\tan\frac{1}{2}\,kl = \frac{\varepsilon_\perp k}{\sqrt{\varepsilon_s\,(k^2 + \kappa^2)}}; \qquad (10)$$

where $\kappa^2 = \varepsilon_\perp(\hat{A} + gk^2)/4 > 0$; $\hat{A} = A + 3BP_0^2$. The case of interest to us is $\varepsilon_\perp k > \varepsilon_s \kappa$, which is easy to meet in the present case of metallic electrodes. We assume (and check validity later) that $\varepsilon_\perp k/\varepsilon_s \kappa > 1$. Then, the equation simplifies to $kl = \pi$, the same as in FE film without electrodes. Substituting there the above expression

for $(k;\hat{A})$; we find the maximal value of $\hat{A}_c = 2gk_c^2$ at $k = k_c$ where this equality is first met, defining the temperature where the instability sets in. The "polarization wave" forms at $\hat{A} < 0$ such that

$$\hat{A}_c = 2gk_c^2 = A_d = \quad =l; \tag{11}$$

$$k_c = \frac{4^{3}}{{}_{?}gl^2}^{1=4} \frac{1}{{}^{1=4}_{?}\sqrt{d_{at}l}}; \tag{12}$$

where g is the coefficient before the gradient term in the equation of state (9), $= 4^{3=2}g^{1=2}=_{?}^{1=2}$ $d_{at}=_{?}^{1=2}$ is the characteristic thickness for the domains formation. Now, checking the assumption that we used to solve the Eq. (10), we see that it boils down to $\sqrt{4 _{?}}=\sqrt{_s{}^2g}$ $\sqrt{4 _{?}}=_s > 1$; which is met in (e.g. perovskite) films with $_{?}$ 100 1000; and the typical $_s$ 1 10:

These results remain basically unchanged if one were to account for realistic boundary conditions and the fact that the interface creates the effective "field" w coupled to the normal polarization component [11]. The surface field results in a "frozen" polarization $P_0(z)$; but since it extends over a short length on the order of a lattice spacing, it makes the film response "hard" just near the boundary. The film remains "soft" in the bulk and there the stability loss proceeds by the above scenario via appearance of the polarization wave. The effect of the surface field is basically that the surface layer of atomic thickness would be excluded from the process of domain formation.

Importantly, in nearly unstrained cubic ferroelectric films the multidomain states are much more likely than in standard uniaxial ferroelectrics. Indeed, upon cooling from the paraelectric phase of a uniaxial ferroelectric film a domain instability sets in a form of a "polarization wave" when $A = A_d$ (11) with the critical wave vector $k = k_c$ (12) found from

$$jA_djuniaxial = 4^{3=2}g^{1=2}=_{?}^{1=2}l; \tag{13}$$

Eq. (11), where $_{?} = 1+ 4 =A_{?}$ is the dielectric constant in the direction perpendicular to ferroelectric axis in the plane of the film. This is the case of interest to us, since $_{?}$ 10^3 in $BaTiO_3$ at 2% lattice misfit [18,7]. In standard situations Eq.(13) applies, but if cubic perovskite films are grown on a substrate with small to negligible lattice mismatch, the period of a domain structure in a cubic ferroelectrics would increase. At the limit of applicability of this formula one can estimate $A_{?}$ A_k gk_c^2 and we will call them "near-cubic". Substituting this into (13), we obtain k_c $=(2^{1=2}l)$ $1=l$; so that the domain width a k_c^{1} tends to become comparable to the thickness of the film. In this case, according to (13), the transition occurs very near the bulk critical temperature at

$$jA_djnear\,cubic \quad g=\hat{l} \quad (d_{at}=l)^2: \tag{14}$$

The minimal thickness, where the near cubic thin films can still transform into a polydomain ferroelectric state, is then estimated for e.g. $BaTiO_3$ as l_{cd} $d_{at}(\max jA_djnear\,cubic)^{1=2}$ $6d_{at}$ 10Å at low temperature. Therefore, the ferroelectricity in near cubic ferroelectric films can exist in a polydomain form down to "atomic" thicknesses (just about one unit cell thick), where the present continuous theory is at the border of validity but still able to produce semiquantitative results. One can estimate from (13) that this regime corresponds to $_{?}$ $4\hat{l}=g$ $(l=d_{at})^2$. A more careful consideration suggests that the transition in a cubic ferroelectric film with a smaller lattice misfit with the substrate than the above borderline value proceeds into a monodomain state with homogeneous in-plane polarization, e.g. P_x. This threshold misfit is very small indeed, so in most cases the film remains uniaxial and splits into domains according to the above scenario.

One can identify two possible cases from Eqs. (4) and (11), while considering possible phase transitions upon lowering temperature: (i) $A_h > A_d$; when $> L_0$; the phase transition is into a homogeneous state, and (ii) $A_h < A_d$ when $< L_0$; the phase transition proceeds into a multidomain state. The case (i) does not mean that the state remains homogeneous. It is stable with respect to inhomogeneous fluctuations, but when the temperature approaches A A_d; domains would start to form. Indeed, at this point the domain wall thickness W $\sqrt{g=A_d}$ becomes smaller to the domain width a; $W < a$; and the existence of usual domains becomes possible. The situation with metallic electrode is analogous to a system with dead layers, which is metastable far from the critical point at jAj jA_dj with respect to domain structure at any thickness of the dead layer [16], and the domains are likely to form already at A A_d: Consider now the case (ii) $< L_0$; where paraphase becomes unstable with respect to domains close to the phase transition point. Interestingly, it was found in Ref. [14] that the homogeneous state may be stable with respect to small inhomogeneous fluctuations not only in the paraphase but also in the ferrophase at some $T < T_s$: This result is formal, however, since the system is likely metastable in this region and domains will grow. The temperature T_s is defined by the condition $A + 3B P_0^2 = A_d = \quad =l$: For the case $g = \quad = 0$ this corresponds to a point where a depolarizing field equals thermodynamic coercive field, separating bulk homogeneous metastable from unstable states. At $T < T_s$ and negligible energy of the domain walls ($g = 0$) the depolarizing field would split the FE film into domains. Therefore, the homogeneous state below T_s is actually metastable, and this is also easy to prove by comparing its free energy with the domain state. The case with $g \neq 0$ is more involved, but should be qualitatively similar, so that the low-temperature ho-

mogeneous state predicted in Ref. [14] is actually unobservable in the thermodynamic sense.

It has been found in first-principles modeling of $BaTiO_3$ ferroelectric film with $SrRuO_3$ metallic electrodes with in-plane lattice parameter corresponding to a $SrTiO_3$ substrate (i.e. mimicking a capacitor structure grown on top of $SrTiO_3$ with 2% compressive strain) that the state with a homogeneous polarization in c direction remains stable down to 2Å at zero temperature [7] (10Å in unstrained $PbTiO_3$ [19]). Further, it was claimed that the depolarizing field was solely responsible for vanishing of the ferroelectricity in thinner films, the chemistry of the interface (within the present nomenclature: the additional boundary conditions, ABC) was deemed unimportant (however, see [19]).

With regards to such phase transitions with thickness of the film, there are again two possibilities for samples with the thickness $l = l_h = L_0/|A|$ where $P_0 = 0$: (i) paraelectric state with zero polarization is stable if $A = A_h > A_d$ (i.e. $L_0 <$); and (ii) it is unstable and domains form, $L_0 >$. The condition (i) is met when

$$\frac{\sqrt{4}}{?} = \frac{\sqrt{}}{s}\frac{}{^2 g} < 1: \qquad (15)$$

For very moderate values for perovskites $_?$ 100 1000; the electrode dielectric constant should then be $_s >$ 10 30; which may or may not hold for particular electrodes. This condition has not been checked in [7] and, therefore, it remains unclear what regime corresponds to the phase transitions studied in [7]. We see that the assumption about the existence of homogeneous state made in [7] is highly questionable and most likely the film in the ground state would be split into domains. When the condition (15) is met [case (i)], the film is in a paraelectric phase when $l < l_h$ (see, however, a reservation below) and becomes single domain ferroelectric in thicker films, $l > l_h$; Fig. 1b. Indeed, at $l > l_h$ we have $A \hat{} A_d = 2L_0 \left(\frac{1}{l_h} - \frac{1}{l}\right) + \frac{L_0}{l} > 0$ and the homogeneous state remains stable with regards to small inhomogeneous fluctuations. However, it should become metastable at $l > l_d$, where domains become possible, i.e. $W <$ a; which happens at $l > l_d$; $l_d \left(\frac{g}{?}\frac{l_h}{L_0}\right) \left(\frac{l_h}{L_0}\right) > l_h$: The paraelectric phase is stable at $l < l_h$ with respect to small fluctuations but may, at least in some cases, be metastable [14].

In the second case one has $L_0 >$; so that $l_d < l_h$; and in films thinner than l_h the paraphase is already unstable with respect to domains. Certainly, domains would form in thicker films too, so there is no chance that the film can become homogeneously polarized. Summarizing, we see, that the film can transform with increasing thickness (i) from paraphase into homogeneous ferrophase at $l_h < l < l_d$ (which in some cases may be metastable), and then into domain state at $l > l_d$, or (ii) the paraphase goes over directly into domain state at $l > l_d$:

Now, we would like to see the effect of a finite band gap E_g and free carriers in the ferroelectric itself on stability of homogeneous state. One sees from Eq. (3) that at

$$P > E_g/qL_0; \qquad (16)$$

where E_g is the band gap of the FE, the depolarizing field in the FE exceeds $|E_d| \quad E_g/ql$, the band bending in the film becomes larger than $E_g/2$; and pockets with degenerate screening carriers form in atomically thin layers at the interface [3]. We can rewrite this into a more useful form $P > \ _s P_{at} \ d_{at}(E_g/8 \ E_{at})$; where $P_{at} = q/d_{at}^2 \quad 200 \ C/cm^2$ is the "atomic" polarization, $E_{at} = q^2/d_{at} \quad 10eV$ the "atomic" energy. For metallic contacts ($_s$ 1 3; d_{at} 1), and a typical band gap in FE $E_g = 2 \quad 3eV$ the condition is $P > 10 \quad 20 \ C/cm^2$, so it seems as if it can be met in many ferroelectrics of interest not very close to the phase transition. However, the system will split into domains close to T_c and is unlikely to reach such a homogeneous state, for the same reason as in FE film without electrodes or in a film with lightly doped semiconductor electrodes below.

In the FE slab without electrodes, the screening by the carriers is possible only when the depolarizing field again exceeds $|E_d| \quad E_g/ql$; and pockets of screening carriers can form in atomically thin layers at the surface of FE [2]. Before pockets form, the depolarizing field is huge, $E_d = \ 4 \ P$ and it totally suppresses the homogeneous polarization. Therefore, the film cannot get into monodomain state until the absolute value of thermodynamic coercive field becomes $> E_g/ql$. This is certainly not possible until such a low temperature where $|A| > |A_1| = \left(\frac{3^{3=2} B^{1=2} E_g}{2ql}\right)^{2=3}$. Using the estimate $B \quad P_{at}^2; P_{at} \quad q/d_{at}^2$; we obtain

$$|A_1| \quad \frac{3^{3=2} E_g}{2k_B T_{at}} \left(\frac{d_{at}}{l}\right)^{2=3} \quad \left(\frac{d_{at}}{l}\right)^{2=3}; \qquad (17)$$

where k_B is the Boltzmann constant. If this state could be reached, the system would experience a discontinuous transition into a state with large polarization. But it could not, since domains appear much closer to T_c: Indeed, according to Eqs. (11),(17)

$$\frac{A_d}{A_1} \quad \frac{1}{\sqrt{?}} \left(\frac{d_{at}}{l}\right)^{1=3} \quad 1: \qquad (18)$$

The result (17) suggests that in typical ferroelectrics thinner than 1–10 m the monodomain state is simply impossible: the equation of state has only a trivial solution $P = 0$. Similar reasoning applies to the case of intrinsic semiconductor electrodes [5,4], where E_g now means the band gap of the semiconductor. These authors have found that the transition into a homogeneous state should become first order but did not realize that it

cannot compete with domains. The above results are in striking disagreement with claims [8] that carriers can stabilize the homogeneous polarization in the few-nm thick FE films with semiconductor electrodes. There is no comment on a disagreement with earlier calculations by Ivanchik and Guro et al. [2], who obtained the results by solving the equation of state, accounting for presence of the pockets with degenerate carriers that were disregarded in [8].

We have shown that carriers in either ferroelectric itself or semiconductor electrodes are usually insufficient to screen the depolarizing field not far from the phase transition. Far from the transition other mechanisms of screening may operate, e.g. generation of bulk/surface charged defects like oxygen vacancies [20], surface reconstruction [21], or local charge disproportionation between ion layers [22,20]. Yet, the formation of domains seems to be the dominant screening mechanism in ferroelectric films, at least near the phase transition. Our results suggest that nearly unstrained cubic ferroelectrics go over into a multidomain state upon cooling to below the critical temperature especially easily. In certain cases (perhaps, not observed yet) they could transform into a monodomain state. In a multidomain state, the electric response of the film would be determined by the properties of the domain structure, including pinning. In this regard, it may be relevant to the present discussion that in 12Å $PbTiO_3$ thin films on $SrTiO_3$ substrate the Argonne group has detected domains [23]. In their case the top electrode was absent, but we know that the conditions for the domain formation in non-electroded films are similar to those in electroded samples (capacitors) if one takes into account possible dead layers or finite screening length in the electrodes, see above discussion of Eq. (11). Theoretically, at least, the ferroelectric domains may survive down to thicknesses comparable to one unit cell.

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